X7S Dielectric



General Specifications



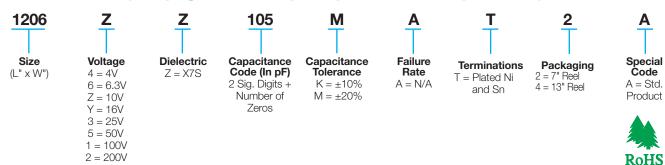
GENERAL DESCRIPTION

X7S formulations are called "temperature stable" ceramics and fall into EIA Class II materials. Its temperature variation of capacitance s within $\pm 22\%$ from -55°C to ± 125 °C. This capacitance change is non-linear.

Capacitance for X7S varies under the influence of electrical operating conditions such as voltage and frequency.

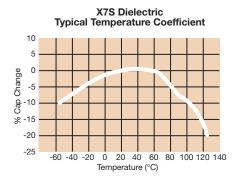
X7S dielectric chip usage covers the broad spectrum of industrial applications where known changes in capacitance due to applied voltages are acceptable.

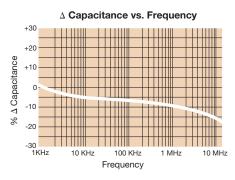
PART NUMBER (see page 2 for complete part number explanation)

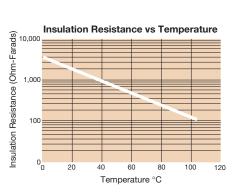


NOTE: Contact factory for availability of Tolerance Options for Specific Part Numbers.

TYPICAL ELECTRICAL CHARACTERISTICS

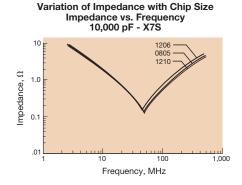


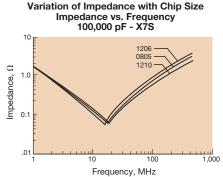




Impedance vs. Frequency 1,000 pF vs. 10,000 pF - X7S 0805 10.00 pF 1,000 pF 10,000 pF 10,000 pF 10,000 pF 1000 pF

Variation of Impedance with Cap Value





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Specifications and Test Methods

Parameter/Test		X7S Specification Limits	Measuring Conditions					
Operating Temperature Range		-55°C to +125°C	Temperature Cycle Chamber					
Capacitance Dissipation Factor		Within specified tolerance ≤ 5.0% for ≥ 100V DC rating ≤ 5.0% for ≥ 25V DC rating ≤ 10.0% for ≥ 10V DC rating ≤ 10.0% for ≤ 10V DC rating	Freq.: 1.0 kHz ± 10% Voltage: 1.0Vrms ± .2V For Cap > 10 µF, 0.5Vrms @ 120Hz					
Insulation I	Resistance	100,000MΩ or 1000MΩ - μ F, whichever is less	Charge device with rated voltage for 120 ± 5 secs @ room temp/humidity					
Dielectric Strength		No breakdown or visual defects	Charge device with 300% of rated voltage 1-5 seconds, w/charge and discharge curn limited to 50 mA (max)					
Resistance to Flexure Stresses	Appearance	No defects	Deflection	n: 2mm				
	Capacitance Variation	≤ ±12%	Test Time: 30 seconds 7 1mm/sec					
	Dissipation Factor	Meets Initial Values (As Above)	V	V				
	Insulation Resistance	≥ Initial Value x 0.3	itial Value x 0.3					
Solderability		≥ 95% of each terminal should be covered with fresh solder	Dip device in eutectic solder at 230 \pm 5°C for 5.0 \pm 0.5 seconds					
Resistance to Solder Heat	Appearance	No defects, <25% leaching of either end terminal						
	Capacitance Variation	≤ ±7.5%	Dip device in eutectic solder at 260°C for					
	Dissipation Factor	Meets Initial Values (As Above)	temperature for 24 ± 2					
	Insulation Resistance	Meets Initial Values (As Above)	hours before measuring electrical properties.					
	Dielectric Strength	Meets Initial Values (As Above)						
Thermal Shock	Appearance	No visual defects	Step 1: -55°C ± 2°	30 ± 3 minutes				
	Capacitance Variation	≤ ±7.5%	Step 2: Room Temp	≤ 3 minutes				
	Dissipation Factor	Meets Initial Values (As Above)	Step 3: +125°C ± 2°	30 ± 3 minutes				
	Insulation Resistance	Meets Initial Values (As Above)	Step 4: Room Temp	≤ 3 minutes				
	Dielectric Strength	Meets Initial Values (As Above)	Repeat for 5 cycles and measure after 24 ± 2 hours at room temperature					
Load Life	Appearance	No visual defects						
	Capacitance Variation	≤ ±12.5%	Charge device with 1.5 rated voltage (≤ 10V) in test chamber set at 125°C ± 2°C					
	Dissipation Factor	≤ Initial Value x 2.0 (See Above)	for 1000 hours (+48, -0)					
	Insulation Resistance	≥ Initial Value x 0.3 (See Above)	Remove from test ch at room temperatu					
	Dielectric Strength	Meets Initial Values (As Above)	before me	easuring.				
Load Humidity	Appearance	No visual defects	Store in a test shamb	or eat at 85°C + 2°C/				
	Capacitance Variation	≤ ±12.5%	Store in a test chamber set at $85^{\circ}C \pm 2^{\circ}C/$ $85\% \pm 5\%$ relative humidity for 1000 hours (+48, -0) with rated voltage applied.					
	Dissipation Factor	≤ Initial Value x 2.0 (See Above)						
	Insulation Resistance	≥ Initial Value x 0.3 (See Above)	Remove from chamber and stabilize at room temperature and humidity for 24 ± 2 hours before measuring.					
	Dielectric Strength	Meets Initial Values (As Above)	24 ± 2 NOURS DE	iore measuring.				

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PREFERRED SIZES ARE SHADED

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SIZE	=	0402		0603		0805		1206		121	0			
Solderi	ing	Reflow/W	/ave	Reflow/Wav	/e Re	flow/Wave	Ref	flow/Wav	re	Reflow	Only			
Packag	jing	All Pap		All Paper		r/Embossed		r/Embos		Paper/Em				
(L) Length	mm (in.)	1.00 ± 0. (0.040 ± 0.0		1.60 ± 0.15 (0.063 ± 0.00		.01 ± 0.20)79 ± 0.008)		20 ± 0.20 26 ± 0.00		3.20 ± (0.126 ±				
(W) Width	mm (in.)	0.50 ± 0. (0.020 ± 0.0		0.81 ± 0.15 (0.032 ± 0.00		.25 ± 0.20 049 ± 0.008)		.60 ± 0.20		2.50 ± (0.098 ±				
(t) Terminal	mm (in.)	0.25 ± 0. (0.010 ± 0.1	15	0.35 ± 0.15 (0.014 ± 0.00	0	.50 ± 0.25 020 ± 0.010)	0.	.50 ± 0.25 .20 ± 0.01		0.50 ± (0.020 ±	0.25			
	WVDC	6.3		6.3	(-	4	10	50	100	6.3				
Cap	100								,					
(pF)	150								_	×				
	220 330		-+		_		├ .			\sim	>			
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	1500 2200								*ŧ	1				
	3300						t							
	4700								1					
	6800													
Cap	0.010													
(μF	0.015 0.022													
	0.022	С												
	0.047	C												
	0.068	С												
	0.10 0.15	С												
	0.15													
	0.33			G										
	0.47			G										
	0.68			G G										
	1.0 1.5			G		N								
	2.2					N								
	3.3					N								
	4.7		- 1			N	Q		Q*					
	10 22		-		-					Z				
	47		- 1											
	100													
	WVDC	6.3		6.3		4	10	50	100	6.3				
	SIZE	0402		0603		0805		1206		121	U			
Letter	А	С	Е	G	J	K	М	N		Р	Q	Х	Υ	
Max.	0.33	0.56	0.71	0.90	0.94	1.02	1.27	1.4		1.52	1.90	2.29	2.54	
Thickness	(0.013)	(0.022)	(0.028)	(0.035)	(0.037)	(0.040)	(0.050)	(0.0)	55)	(0.060)	(0.075)	(0.090)	(0.100)	
Thickness	(0.010)	(/	PAPER			,	, ,	(EMBC	, ,			j

^{*}Contact Factory for Specifications